

# MA4X160 (MA160)

Silicon epitaxial planar type

For high-speed switching circuits

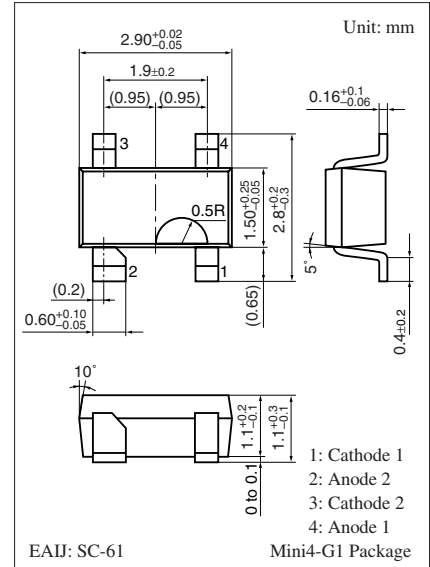
### ■ Features

- Two isolated elements are contained in one package, allowing high-density mounting
- Centrosymmetrical wiring, allowing to free from the taping direction
- Short reverse recovery time  $t_{rr}$
- Small terminal capacitance  $C_t$

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

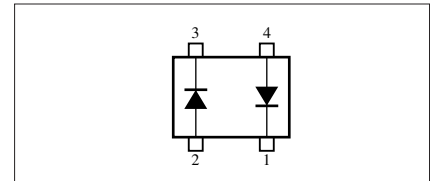
| Parameter                                      | Symbol    | Rating      | Unit             |
|--|-----------|-------------|------------------|
| Reverse voltage                                | $V_R$     | 40          | V                |
| Maximum peak reverse voltage                   | $V_{RM}$  | 40          | V                |
| Forward current<br>(Average)                   | Single    | 100         | mA               |
|  | Double    |             |                  |
| Repetitive peak<br>forward current             | Single    | 225         | mA               |
|  | Double    |             |                  |
| Non-repetitive peak<br>forward surge current * | Single    | 500         | mA               |
|  | Double    |             |                  |
| Junction temperature                           | $T_j$     | 150         | $^\circ\text{C}$ |
| Storage temperature                            | $T_{stg}$ | -55 to +150 | $^\circ\text{C}$ |

Note) \*:  $t = 1 \text{ s}$



Marking Symbol: M1D

Internal Connection



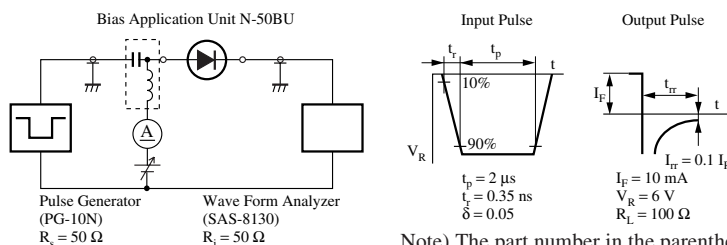
### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter               | Symbol   | Conditions   | Min | Typ  | Max  | Unit          |
|-------------------------|----------|--|-----|------|------|---------------|
| Forward voltage         | $V_F$    | $I_F = 100 \text{ mA}$   |     | 0.95 | 1.20 | V             |
| Reverse voltage         | $V_R$    | $I_R = 100 \mu\text{A}$  | 40  |      |      | V             |
| Reverse current         | $I_R$    | $V_R = 35 \text{ V}$   |     |      | 0.1  | $\mu\text{A}$ |
| Terminal capacitance    | $C_t$    | $V_R = 0 \text{ V}, f = 1 \text{ MHz}$   |     | 0.9  | 2.0  | pF            |
| Reverse recovery time * | $t_{rr}$ | $I_F = 10 \text{ mA}, V_R = 6 \text{ V}$<br>$I_{tr} = 0.1 I_R, R_L = 100 \Omega$ |     |      | 3    | ns            |

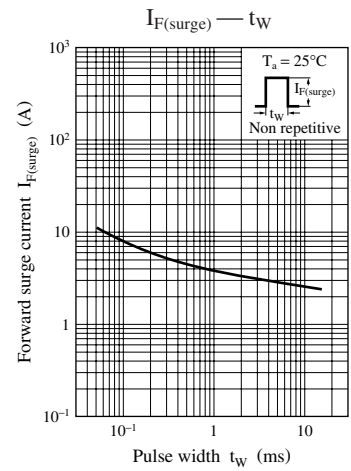
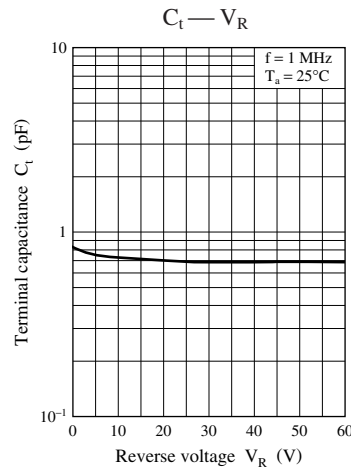
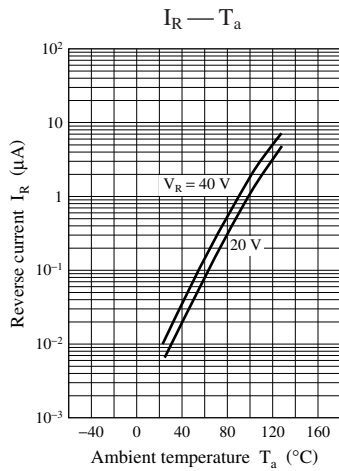
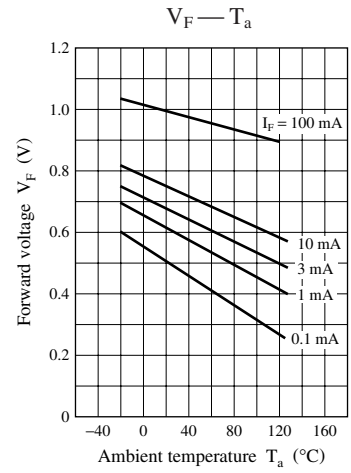
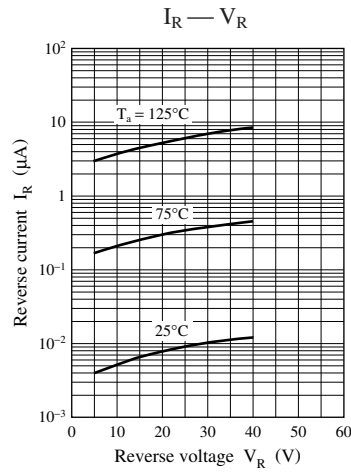
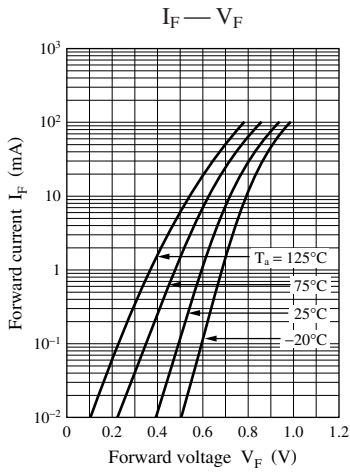
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring method for diodes.

2. Absolute frequency of input and output is 100 MHz.

3. \*:  $t_{rr}$  measurement circuit



Note) The part number in the parenthesis shows conventional part number.



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